

< X/Ku band internally matched power GaAs FET >

MGFK33V4045

14.0 - 14.5 GHz BAND / 2W

DESCRIPTION

The MGFK33V4045 is an internally impedance-matched GaAs power FET especially designed for use in 14.0 – 14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Internally matched to 50(ohm) system

- Flip-chip mounted
 High output power
 - P1dB=2.0W (TYP.) @f=14.0 14.5GHz
- High linear power gain
 - GLP=7.0dB (TYP.) @f=14.0 14.5GHz
- High power added efficiency
 - P.A.E.=22% (TYP.) @f=14.0 14.5GHz

APPLICATION

• 14.0 - 14.5 GHz band power amplifiers

QUALITY GRADE

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=8V • ID=700mA Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Parameter	Ratings	Unit
Gate to drain breakdown voltage	-15	V
Gate to source breakdown voltage	-15	V
Drain current	1800	mA
Reverse gate current	-5	mA
Forward gate current	10	mA
Total power dissipation	17	W
Cannel temperature	175	°C
Storage temperature	-65 to +175	°C
	Gate to drain breakdown voltage Gate to source breakdown voltage Drain current Reverse gate current Forward gate current Total power dissipation Cannel temperature	Gate to drain breakdown voltage Gate to source breakdown voltage -15 Drain current 1800 Reverse gate current -5 Forward gate current 10 Total power dissipation 17 Cannel temperature 105 Storage temperature -65 to +175

*1 : Tc=25°C

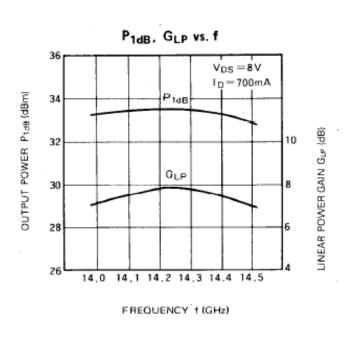
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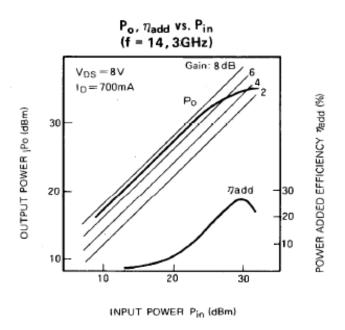
Electrical characteristics (Ta=25°C)

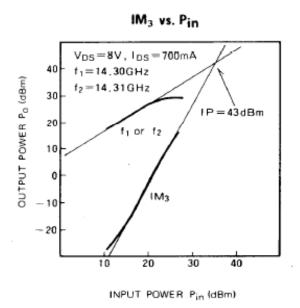
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	1.1	1.8	Α
gm	Transconductance	VDS=3V,ID=700mA	-	600	-	mS
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=4mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=8V,ID(RF off)=700mA	32	33	-	dBm
GLP	Linear Power Gain	f=14.0 – 14.5GHz	5.5	7	-	dB
PAE	Power added efficiency]	-	22	-	%
Rth(ch-c) *2	Thermal resistance	delta Vf method	-	=	10	°C/W

*2 : Channel-case

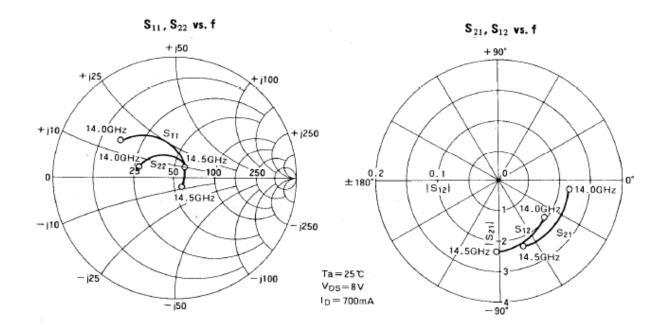
MGFK33V4045 TYPICAL CHARACTERISTICS







MGFK33V4045 S-parameters(Ta=25deg.C , VDS=8(V),IDS=700(mA))



f (GHz)	S Parameters(Typ.)							
	S11		S21		S12		S22	
	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)
14.0	0.50	136	2.28	-10	0.099	-41	0.32	164
14.1	0.38	121	2.35	-25	0.108	-52	0.29	153
14.2	0.27	103	2.39	-38	0.113	-61	0.25	142
14.3	0.19	78	2.43	-51	0.127	-71	0.20	130
14.4	0.13	42	2.37	-62	0.134	-82	0.15	115
14.5	0.18	5	2.29	-72	0.142	-93	0.12	93

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